

U.S. PATENT DOCUMENTS

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| | Α | US- | | | |
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

| * | | Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages) |
|---|---|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| | U | F. Koyama et al., "1.5 W operation of superluminescent diode with highly strained GalnAs/GaAs quantum well emitting at 1.2 μm band"; IEEE 17th International Semiconductor Laser Conference Digest 2000, September 2000, Pages 71 – 72. |
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.